

AMENDMENTS TO THE SPECIFICATION:

In the Title:

Please amend the title as follows:

METHOD FOR MANUFACTURING GALLIUM NITRIDE(GaN) BASED SINGLE CRYSTALLINE SUBSTRATE THAT INCLUDES SEPARATING FROM A GROWTH SUBSTRATE

Please amend the paragraph on page 15, beginning at line 4 as follows:

Further, in this embodiment of the present invention, there may be selectively performed a step of lapping and polishing the lower surface of the GaN based single crystalline bulk 25 separated from the patterned growth substrates 21'. With reference to Fig. 2d, the lower surface of the GaN based single crystalline substrate is mirror-like finished by lapping and polishing, thereby producing a mirror-like finished GaN based single crystalline bulk 25'. When the grooves 26 are formed through the growth substrate 21 as shown in Fig. 2b, the lower surface of the GaN based single crystalline bulk 25 may be damaged. Accordingly, as shown in Fig. 2d, it is preferable to additionally perform a lapping step, in which the damaged lower surface of the GaN based single crystalline bulk 25 is removed and then the lower surface of the GaN based single crystalline bulk 25 is lapped so that the lower surface is planarized, and a polishing step, in which the lower surface of the GaN based single crystalline bulk [[15]]25' is mirror-like finished.

Abstract:

Please replace the current Abstract with the following replacement/amended Abstract